



# THE DESIGN AND DEVELOPMENT OF LOW- AND HIGH-VOLTAGE ASICS FOR SPACE-BORNE CCD CAMERAS

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# Contents

## CCD camera readout electronics system architecture

- Requirements

## CCD video signal processing and digitisation

- CCD video processing ASIC

## CCD DC bias

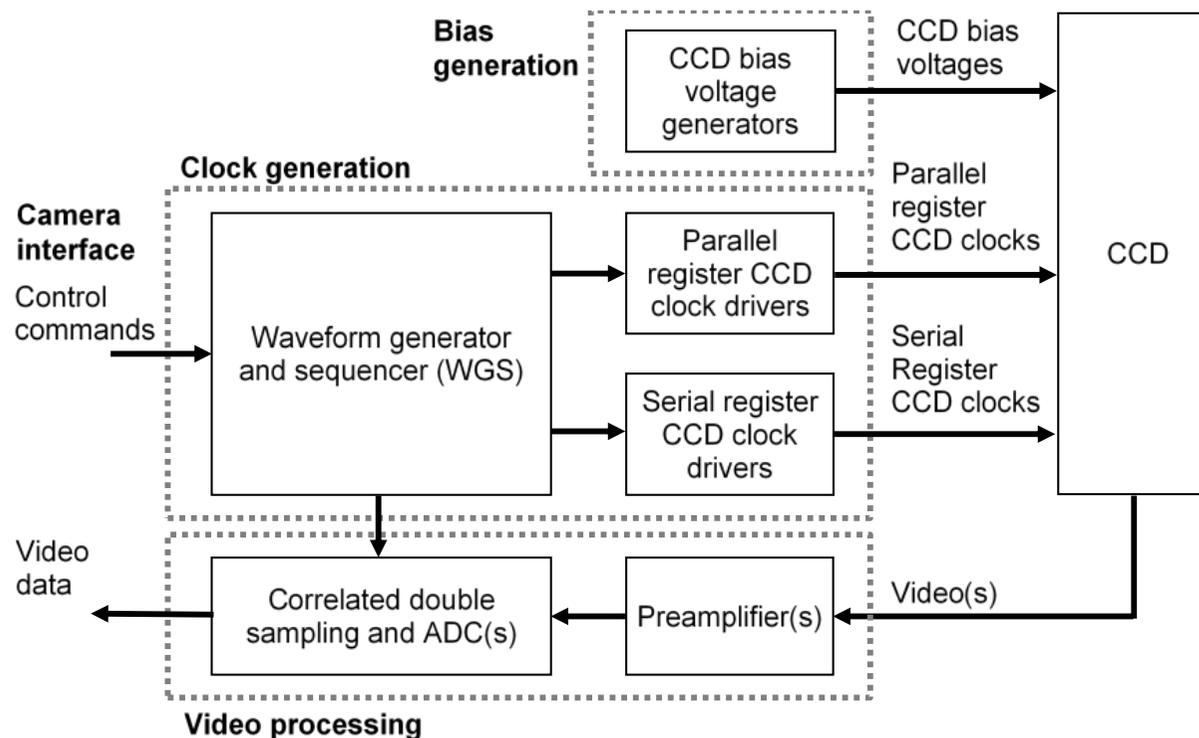
- 8-channel low-voltage DAC ASIC
- Radiation-hardening against single event latchup (SEL)
- 24-channel high-voltage CCD DC bias voltage generator and housekeeping telemetry system ASIC

## CCD clock driving

- 6-channel clock driver ASIC

## Conclusions and future plans

# CCD camera readout electronics system



**Control logic: Generate all timing signals**

- Typically implemented in a radiation-tolerant FPGA

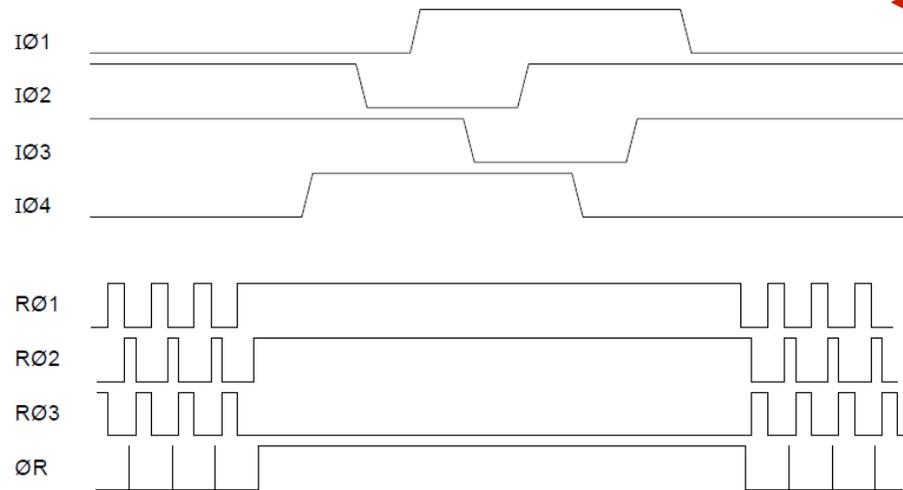
**Multiple-phase CCD clock drivers to clock the signal charge to charge detection amplifiers**

**Low-noise DC bias supplies to operate the CCD's output amplifier(s) and charge drains**

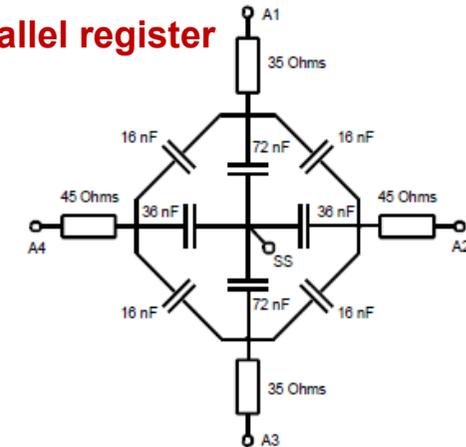
**One or more video preamplifiers, CDS signal processors and analogue-to-digital converters**

# Typical CCD clock waveforms

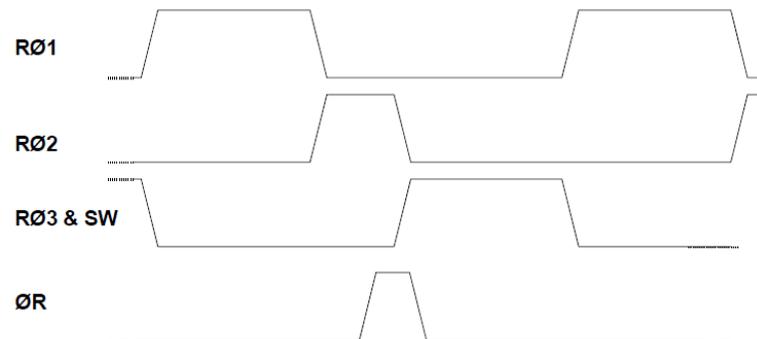
## Parallel clocks



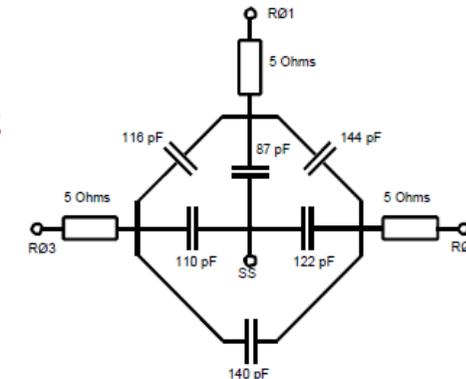
← Amplitude ~ 10 V  
 Frequency ~ 10-100 kHz  
 4k x 2k pixel parallel register  
 Typical loading



## Serial clocks



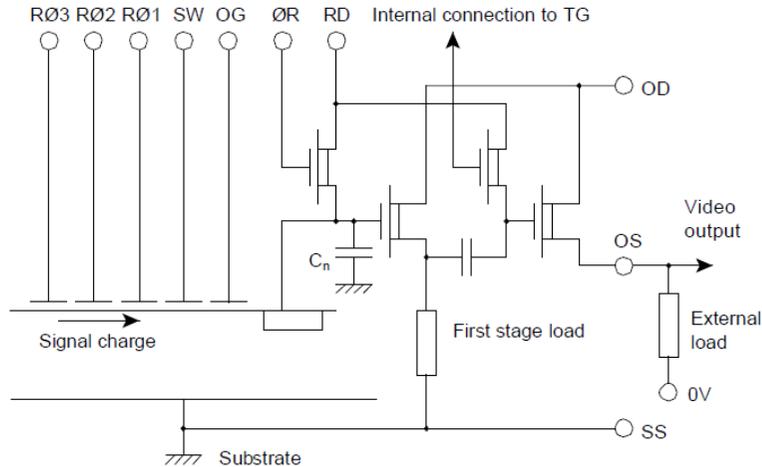
← Amplitude ~ 10 V  
 Frequency ~ 0.1-2 MHz  
 4k pixel serial register  
 Typical loading



**Clock drivers must translate logic-level signals to ~ 10 V amplitude analogue waveforms with sufficient current drive for the CCD's capacitive electrode**

# Output amplifier bias and video output

## Charge detection amplifier

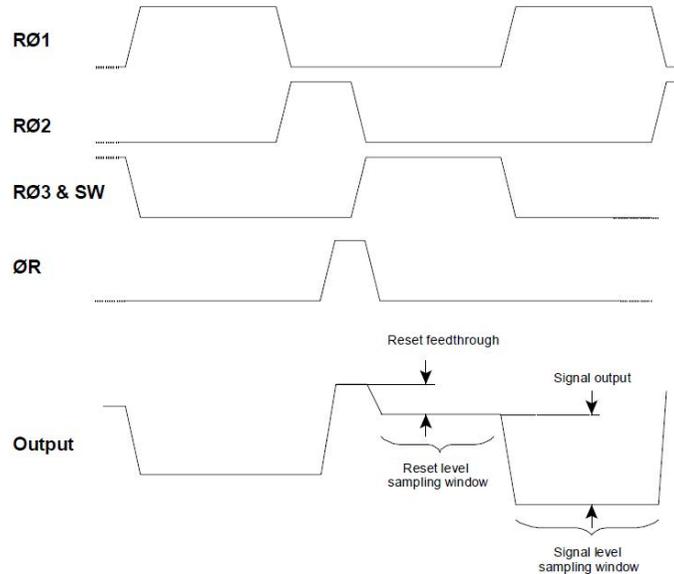


Charge detection amplifier requires several low-noise DC bias voltages

Output Drain (OD) Bias: ~ 30 V

Reset Drain (RD) Bias: ~ 17 V

## Video output waveform



Video output signal swing ~ 1 V

Correlated Double Sampling (CDS)

Signal output = Signal level – Reference level

# Camera electronics design challenges

## System requirements

- Low-volume, low-mass, low-power
- High-reliability and space-qualified components
- Sufficient tolerance to the effects of space radiation

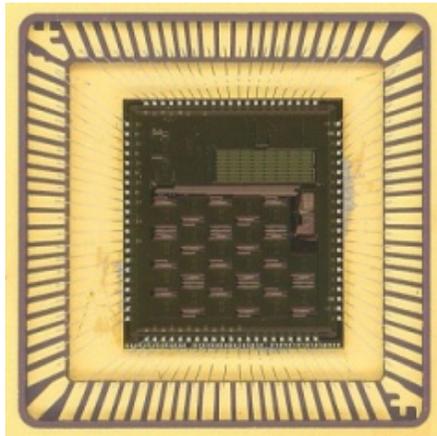
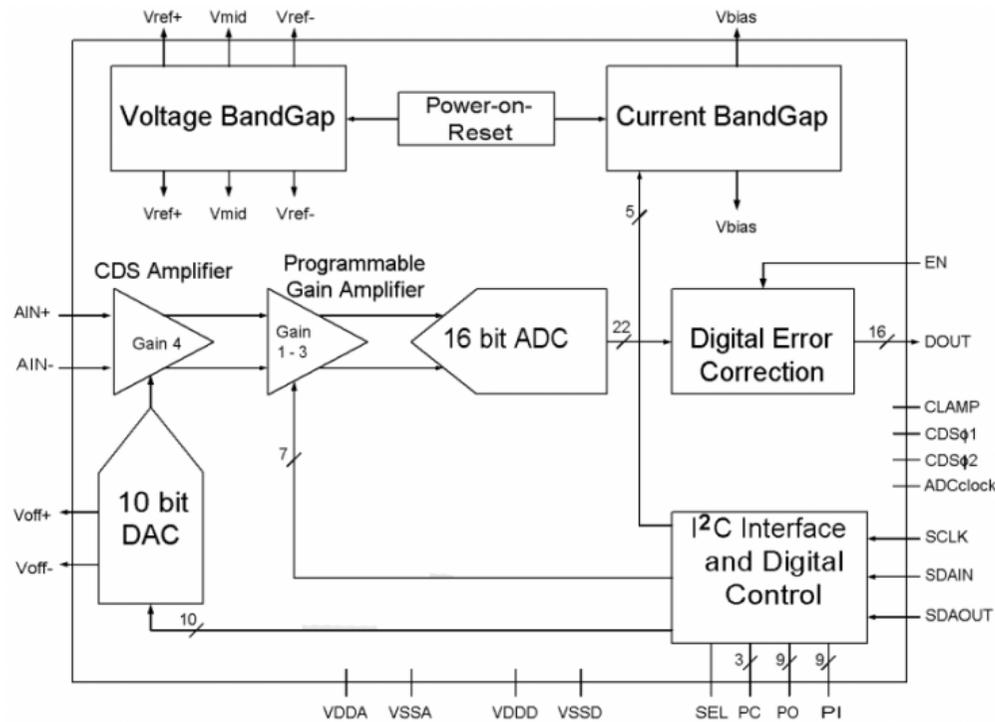
## Electronic component challenges

- Space-qualified components acceptable to international space agencies (ESA/NASA) are frequently unavailable
- Up-screened commercial components may not meet project requirements

## Our approach at the STFC Rutherford Appleton Laboratory

- Design and space-qualification of low- and high-voltage mixed-signal ASICs

# CCD video processing ASIC



## Features

DC Restoration of the CCD video signal

Fully differential-input preamplifier and CDS

1 V video signal input range

Fully differential pipelined 16 bit ADC with digital error correction

Operation at up to at 2 Mpixels/s

10 bit Programmable Offset (+/- 500 mV)

7 bit Programmable Gain (gain = x 1 to x 3)

Input referred system noise: 3 adu rms

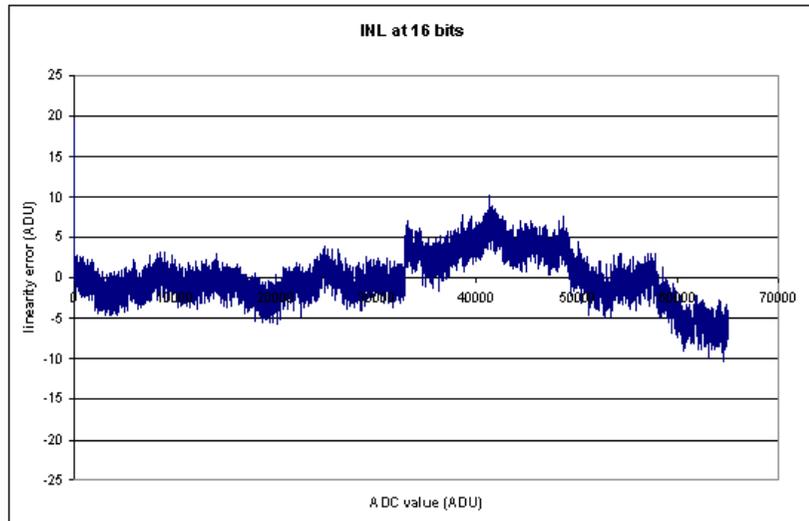
TMR protection against single-event upsets

Power dissipation ~ 400 mW

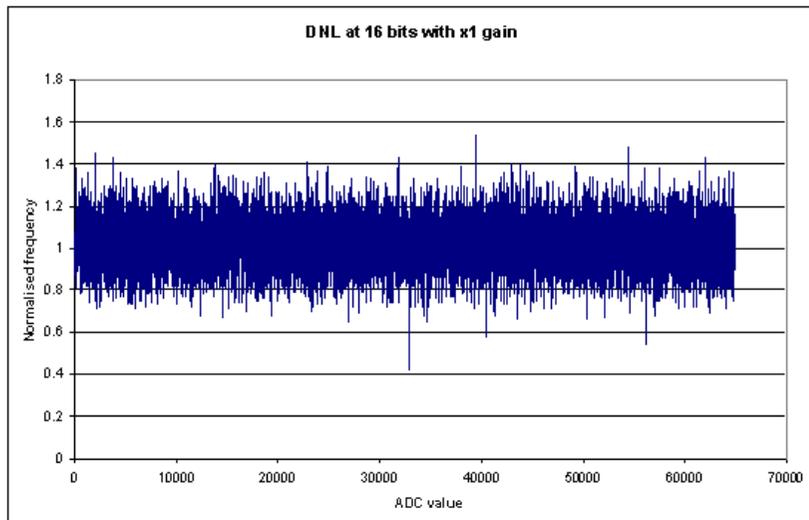
AMS C35 0.35  $\mu\text{m}$  CMOS process

# CCD video processing ASIC

## Integral non-linearity (INL)



## Differential non-linearity (DNL)



## Performance

Video signal input range	= 1 V
Digitisation	= 16 bits
Operation	≤ 2 Mpixels/s
Input referred noise	= 3 adu rms
	= 46 $\mu\text{V}$ rms
e2v CCD203 (4.5 $\mu\text{V}/\text{e}^-$ )	= 10.2 $\text{e}^-$ rms
Integral non-linearity	~ $\pm 10$ LSBs
Differential non-linearity	~ $\pm 0.3$ LSBs
Power dissipation	~ 400 mW

## Radiation test results

Total ionising dose (TID)  $\geq 50$  krad(Si)

SEL LET threshold ~ 14  $\text{MeVcm}^2\text{mg}^{-1}$

SEL linear energy transfer profile (LET) examined to 34  $\text{MeVcm}^2\text{mg}^{-1}$  at Cyclotron Facility of Louvain-la-Neuve in Belgium using  $\text{Ne}^{4+}$ ,  $\text{Ar}^{8+}$  and  $\text{Kr}^{17+}$  ions

# Solar Dynamic Observatory

**NASA's Flagship Solar Mission**

**Launched 11 Feb 2010**

**Atmospheric Imaging Assembly (AIA)**

**Helioseismic and Magnetic Imager (HMI)**

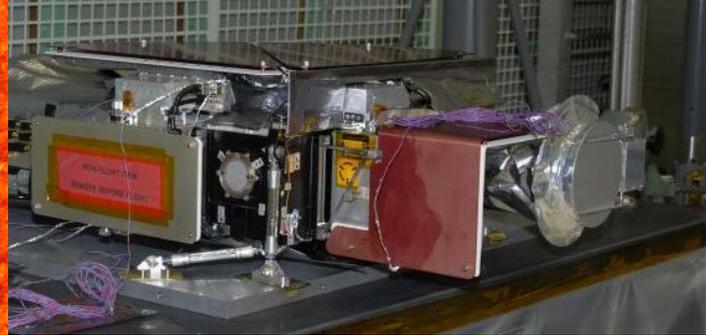
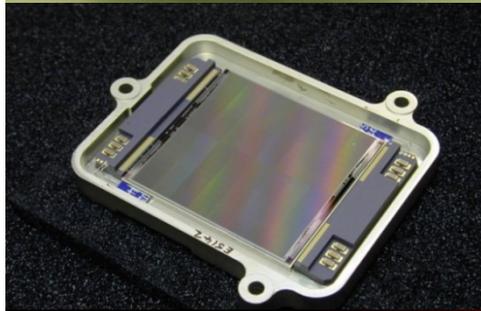
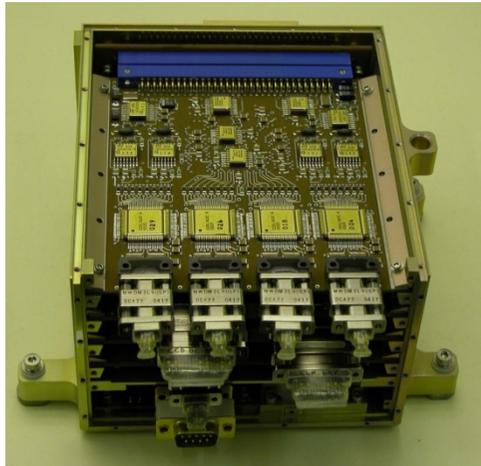
**Custom-designed e2v CCD203**

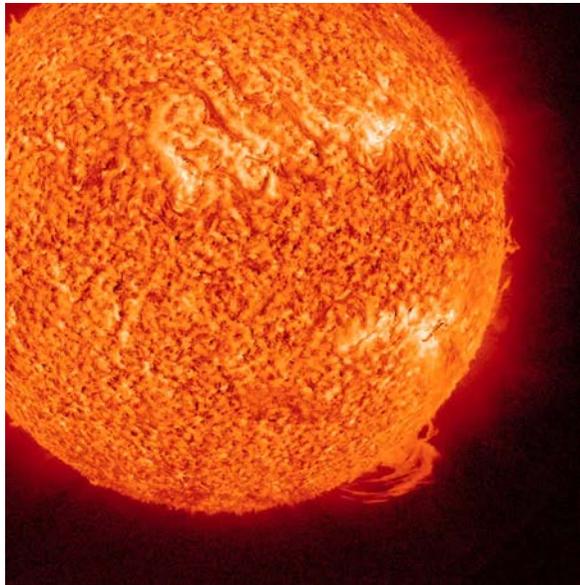
**4k × 4k pixels and 12 μm pixel pitch**

**4-port readout at 2 Mpixels/s each**

**SEL LET threshold ~ 14 MeVcm<sup>2</sup>mg<sup>-1</sup>**

**Video ASICs individually protected with current-sense / current-trip circuitry**



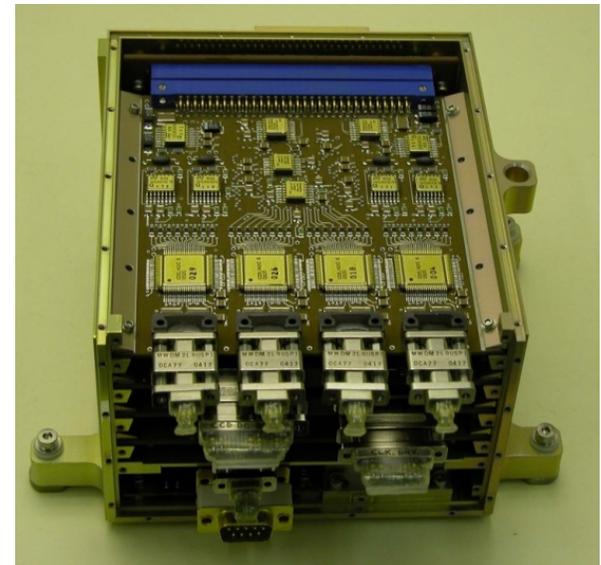


# Progress along a Technology Roadmap

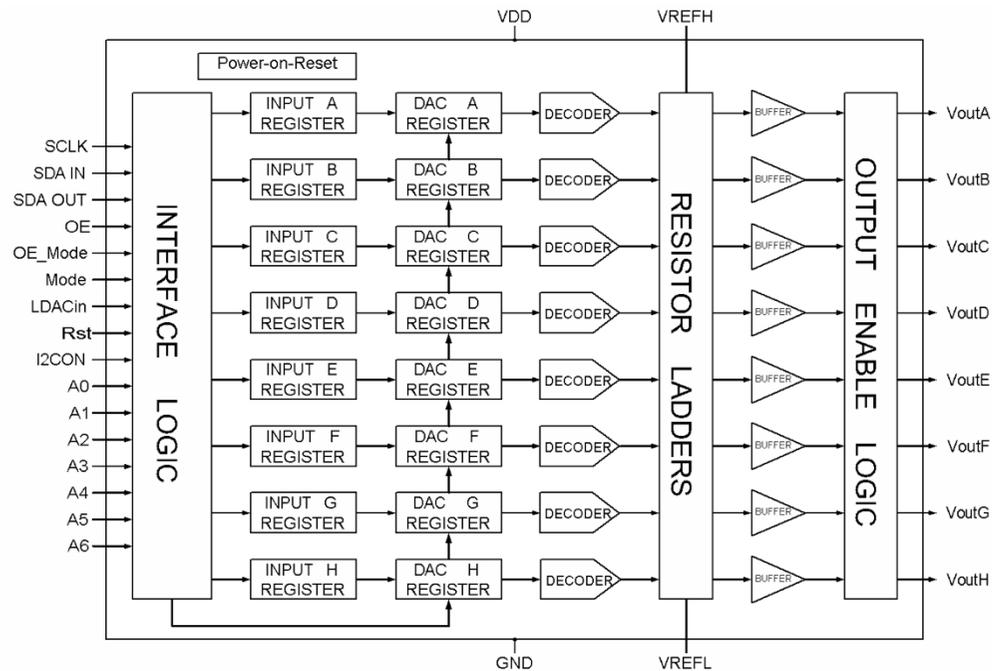
- Have demonstrated Low-voltage CCD ASIC technology
- **But susceptibility to Single-Event Latchup remains**

## Where next?

- Radiation-hardening against SEL
- Greater functional integration
  - High-voltage CCD ASICs



# Low-voltage DAC ASIC



## Features

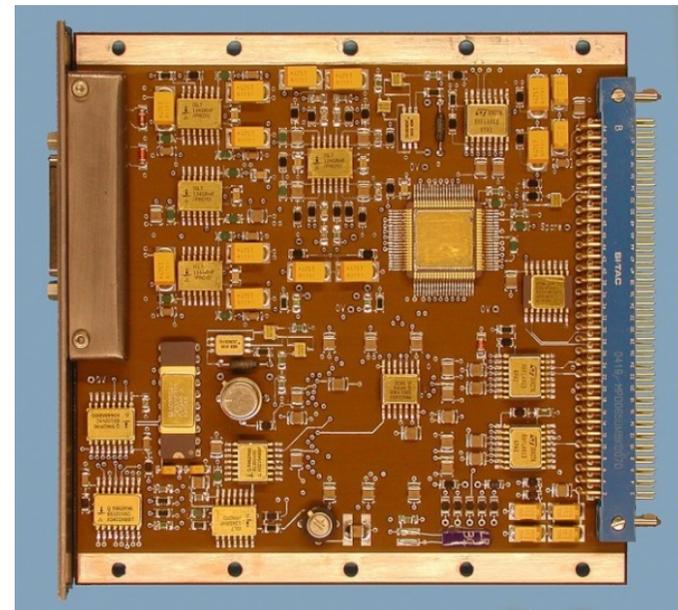
8-channel 10-bit voltage output DACs

Voltage output: 0-2.5 V

Supply: 3.3 V

AMS C35 0.35  $\mu\text{m}$  CMOS process

SEL LET threshold  $\sim 20 \text{ MeVcm}^2\text{mg}^{-1}$



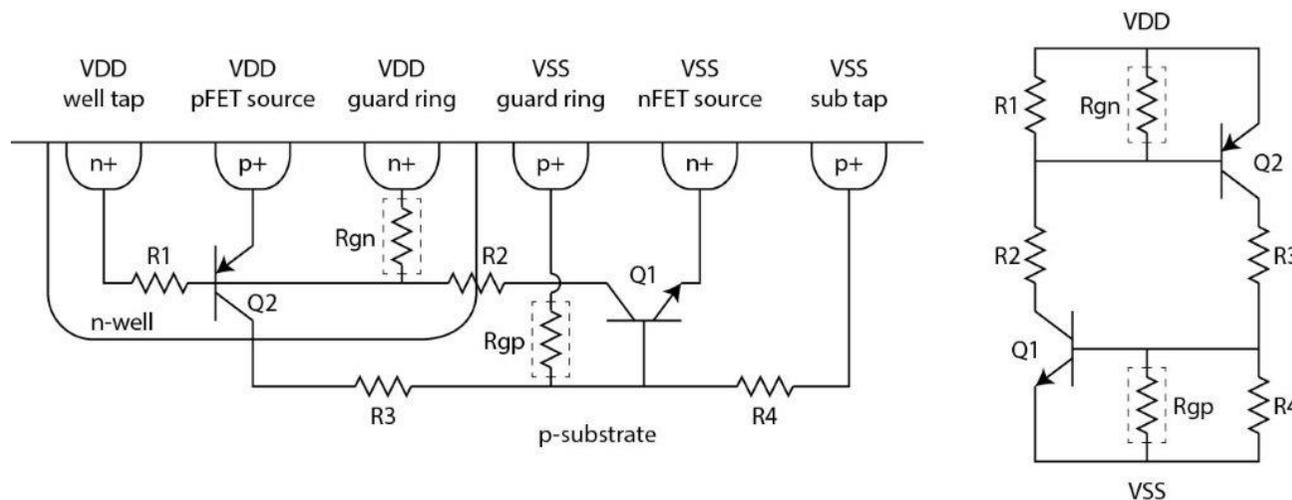
## Flown on NASA's SDO

DAC protected with current-sense and current-trip circuitry

# Guard-Ring Technology

## Latchup

- Latchup is the creation of a low impedance path between the power supply rails
- Latchup is caused by the triggering of parasitic bipolar structures within an IC, in the case of the Space environment, by an energetic particle
- Implanted guard-rings of low-impedance can prevent SEL



## Mk 3 Low-voltage DAC Radiation test results

- No SEL events
- SEL LET threshold  $\geq 130 \text{ MeVcm}^2\text{mg}^{-1}$  Effectively SEL immune

# High-voltage ASICs

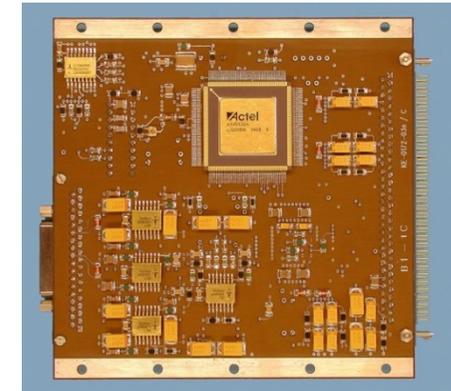
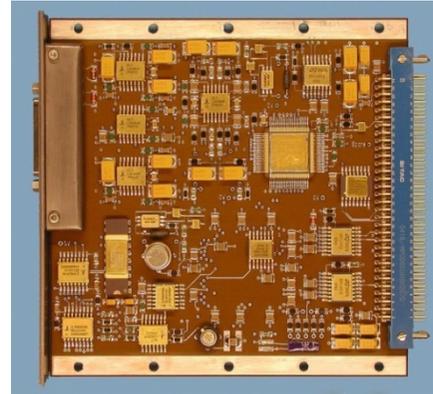
## SDO bias card

120 mm x 120 mm PCB

7 CCD bias voltages set by a DAC ASIC

16-channel housekeeping telemetry

**Something better??**



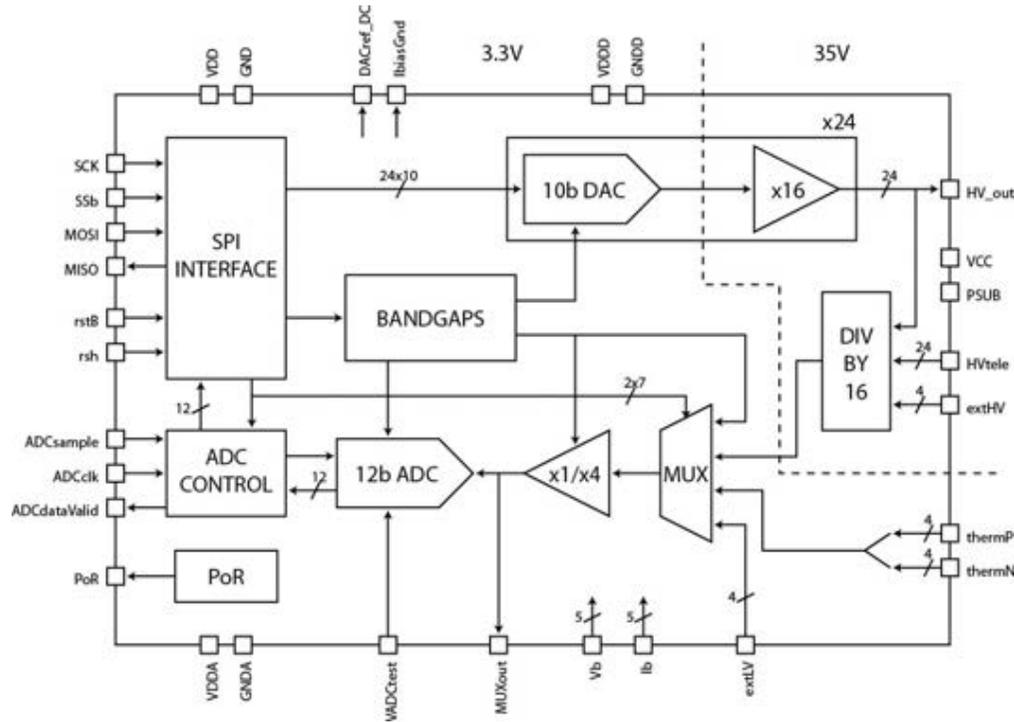
## AMS H35 0.35 $\mu\text{m}$ CMOS process

**Standard 3.3 V transistors and 50 V high-voltage diffused MOSFET (DMOS) transistors**

**3.3 V transistors used within the low-voltage interface logic, voltage references and DACs**

**50 V DMOS transistors to provide the CCD's high-voltage bias supplies directly**

# High-voltage CCD DC bias ASIC (STAR)



## Features

24-channel 10-bit bias voltage outputs

0-32.736 V outputs in 32 mV steps

±20 mA into loads of 10 µF

±25 mA current-limiting short-circuit protection

## Housekeeping telemetry system

36-channel housekeeping telemetry system

Multiplexer, variable gain amplifier, 12-bit ADC

## General

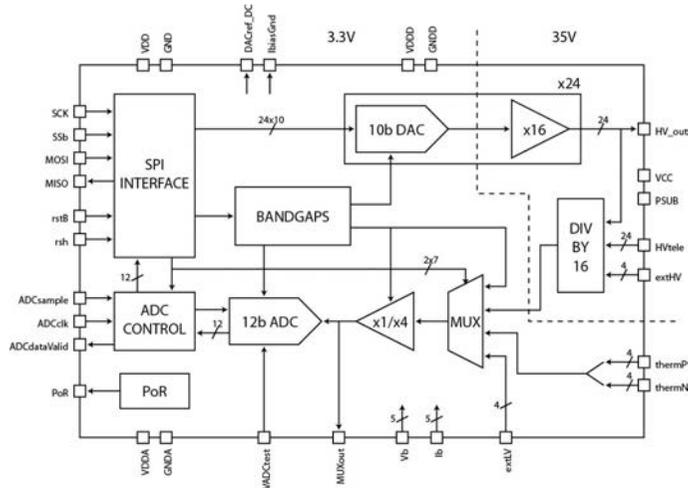
TMR protection against single-event upsets

Guard-ring SEL protected

3.3 V and 35 V supplies

144-pin CQFP

# High-voltage CCD DC bias ASIC (STAR)



**Performance - characterised -40°C to 125°C**

## DACs

**Output noise** ~ 20-40  $\mu\text{V}$  rms (10  $\mu\text{F}$  loading)

**Gain accuracy** < 0.3%

**Integral non-linearity** < 0.6 LSBs

**Quiescent power (at 35 V)** ~ 28 mW per DAC

## Telemetry system

**Integral non-linearity** < 1.3 LSBs

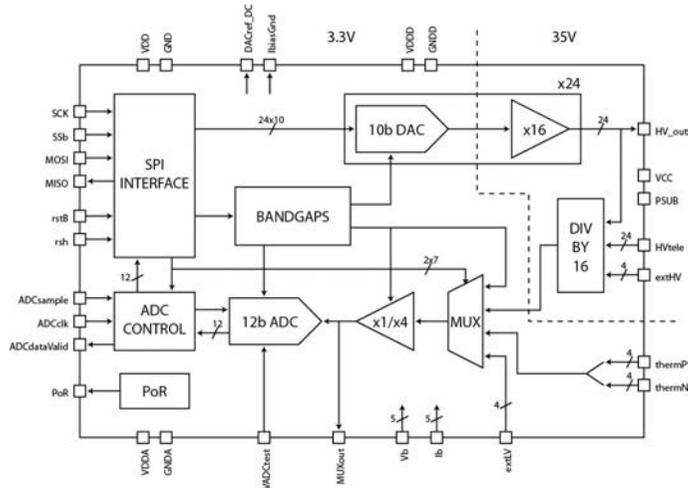
**Differential non-linearity** < 0.5 LSBs

**Sample noise** < 0.75 LSBs rms

## System

**Power dissipation:** = 37 mW to 1.17 W (max)

# High-voltage CCD DC bias ASIC (STAR)



## STAR ASIC

24-channel 10-bit bias voltage outputs with telemetry

36-channel general purpose telemetry system

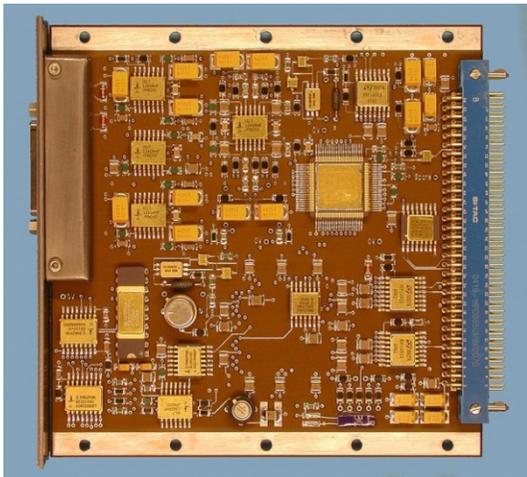
Compared to, or to replace:

SDO bias card

120 mm x 120 mm PCB

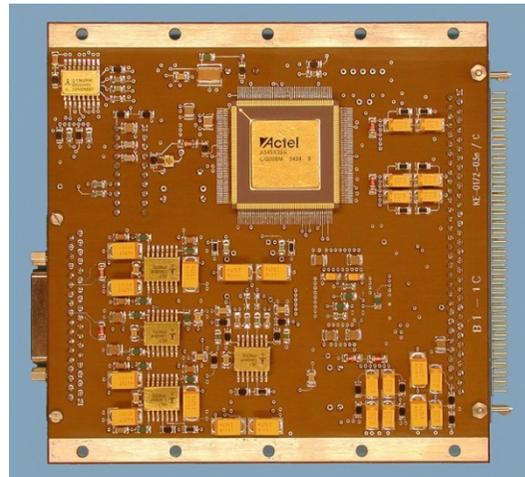
7-channel bias voltages set by low-voltage DAC ASIC

16-channel housekeeping and telemetry



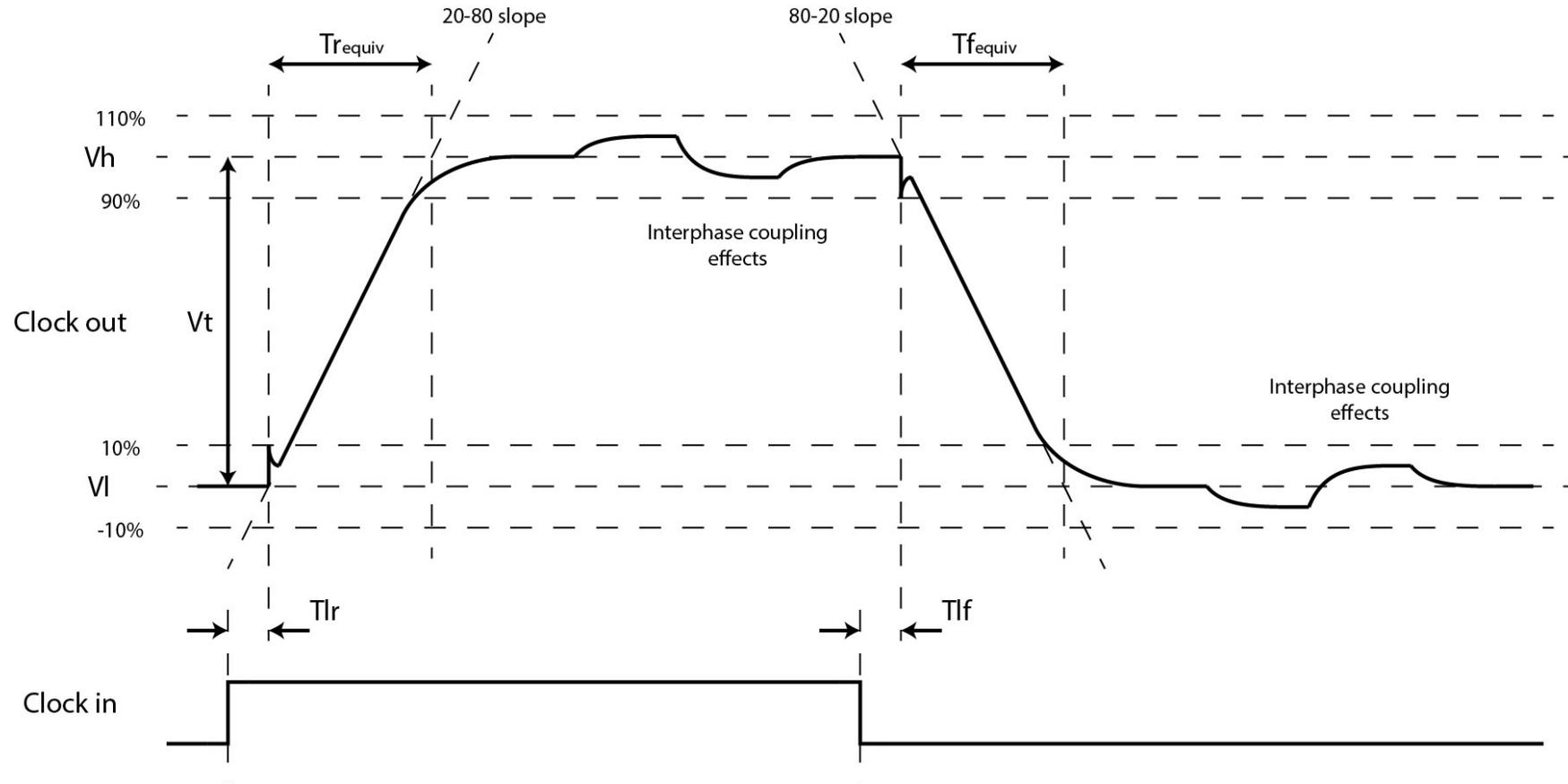
N Waltham

CEOI Emerging Technology Workshop 3-4 May 2017 17

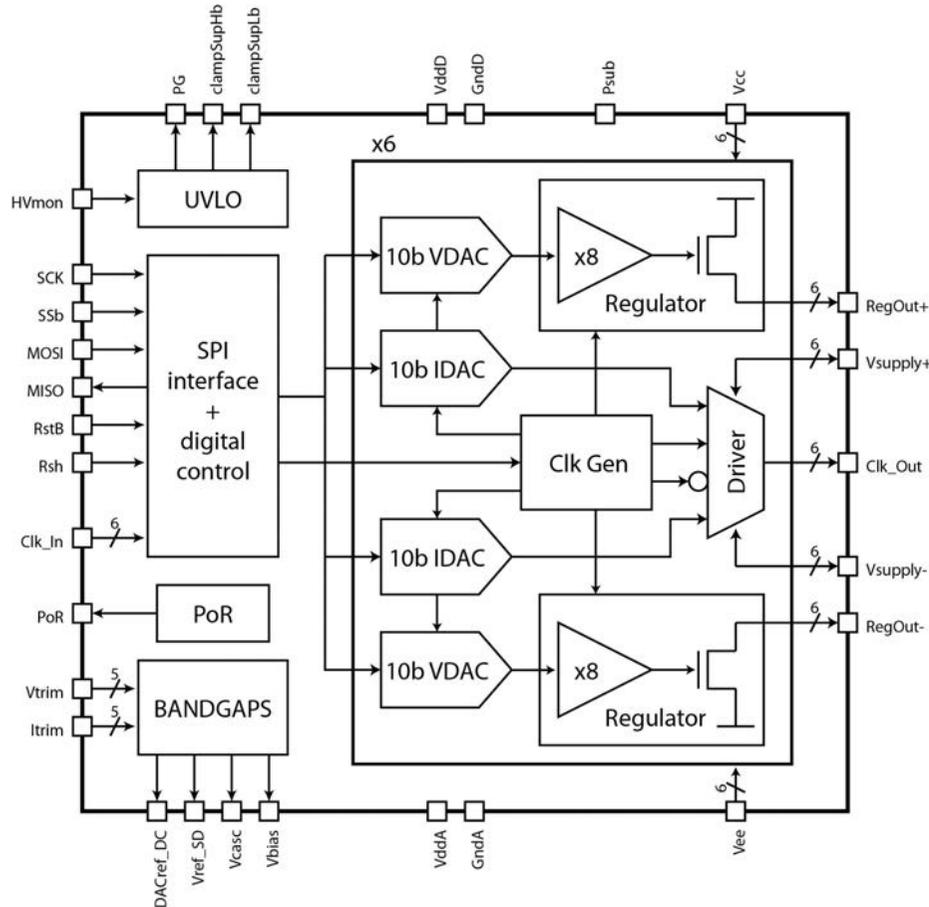


# CCD clock driver ASIC (C2BA)

## CCD clock driver waveform definition



# CCD clock driver ASIC (C2BA)



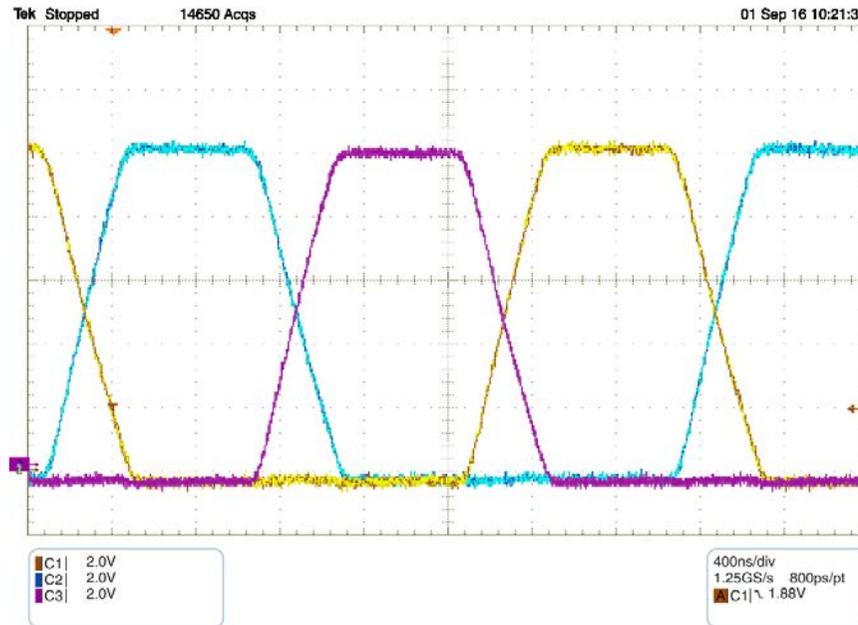
## Features

- 6-channel CCD clock drivers
- 0-16.368 V outputs in 16 mV steps (each)
- 0.4-400 mA output drive current (each)
- 2 pF - 200 nF loads
- 20 ns - 20  $\mu$ s Tr / Tf
- 20-80% linear rise/fall
- <  $\pm$ 10% interphase coupling effects

## General

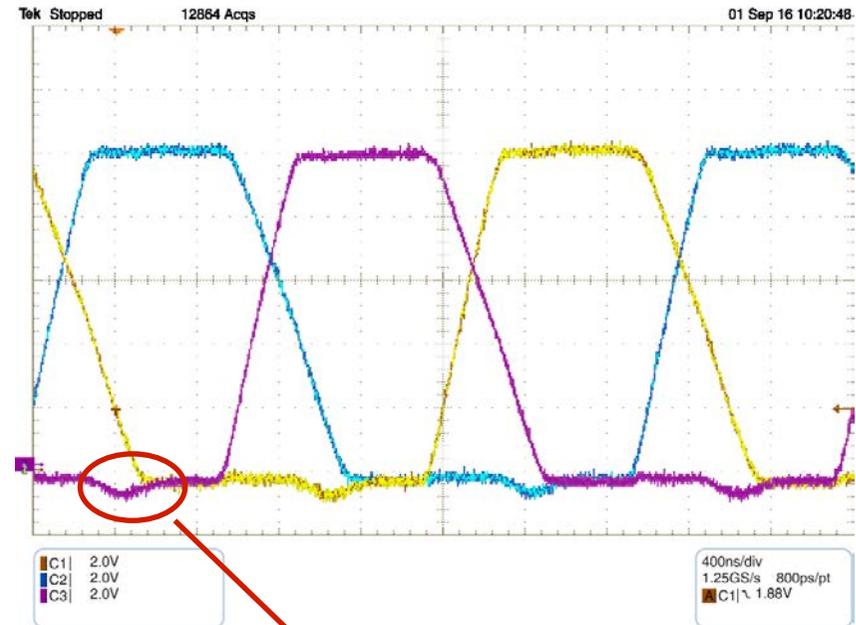
- TMR protection against single-event upsets
- Guard-ring SEL protected
- 3.3 V and 18 V supplies
- 132-pin CQFP

# 3-phase serial register clocks



120 pF to substrate (0 V)  
140 pF interphase coupling capacitance  
10 V clock amplitude  
1 MHz clocking frequency

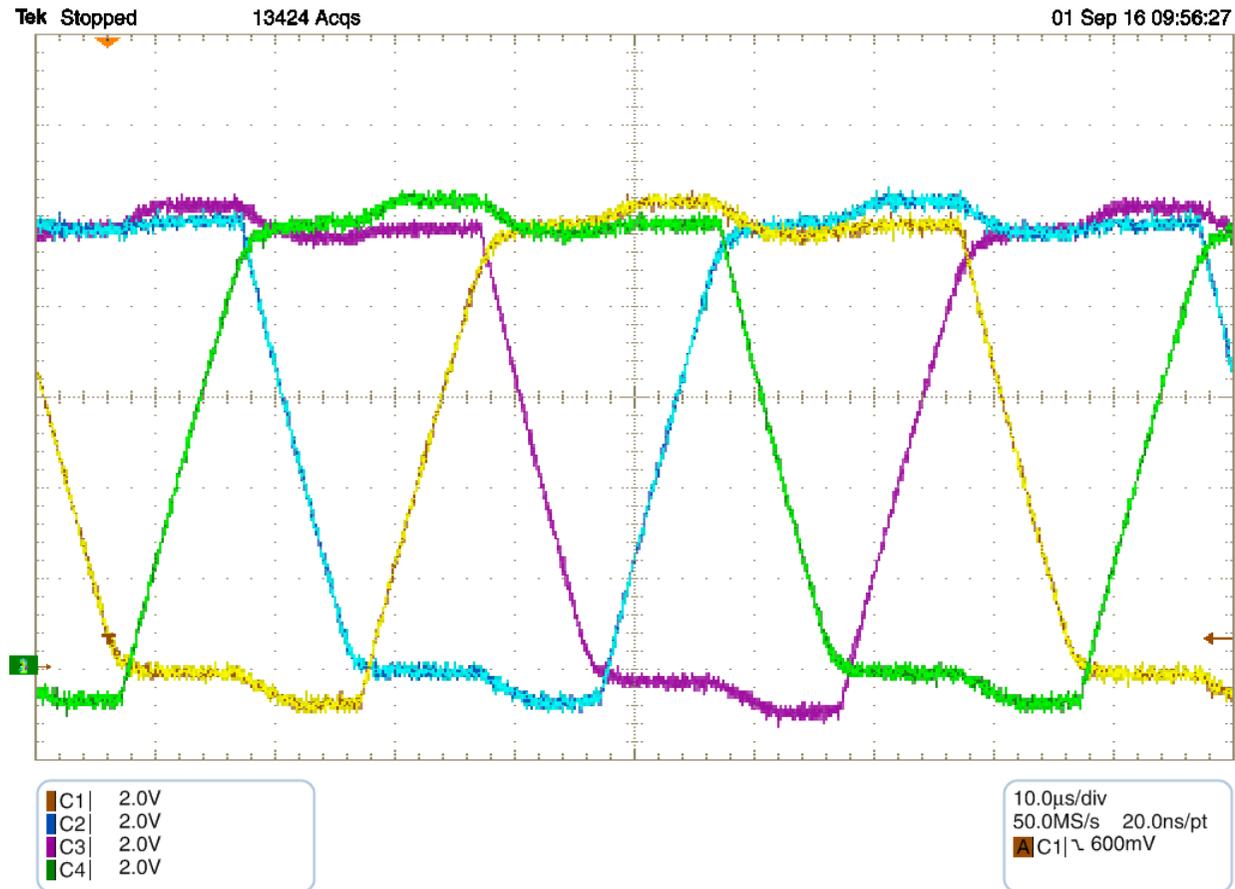
50% clock phase overlap



Small interphase coupling seen on the clock-lows

60% clock phase overlap

# 4-phase parallel register clocks



70 nF to substrate (0 V)

16 nF interphase coupling capacitance

10 V clock amplitude

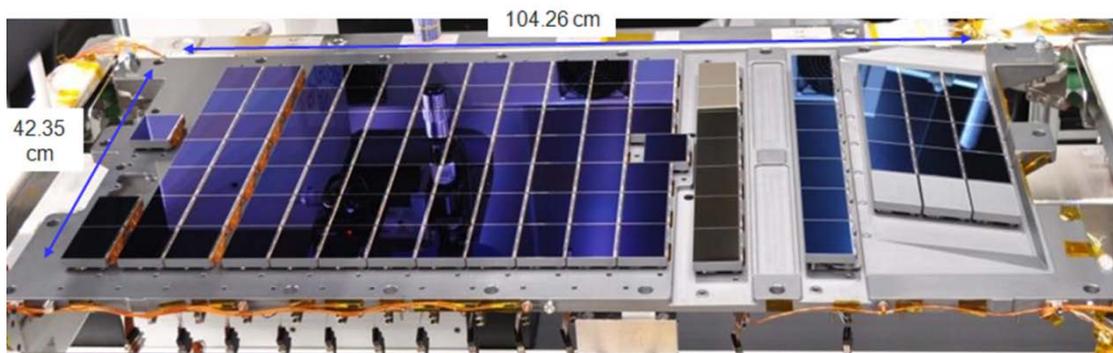
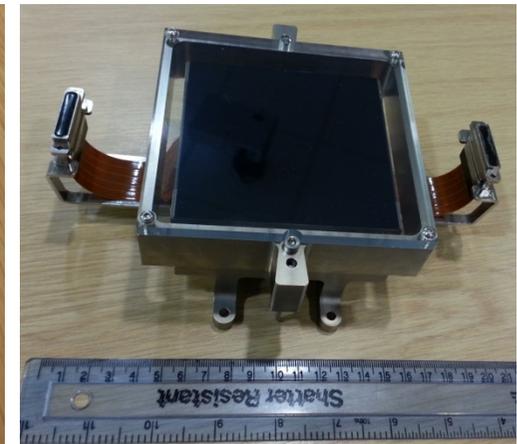
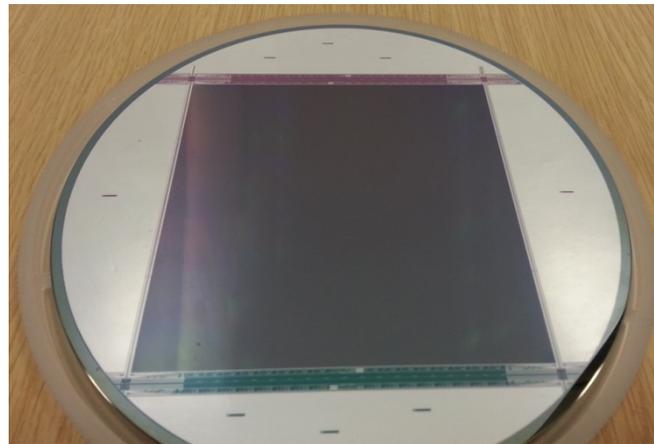
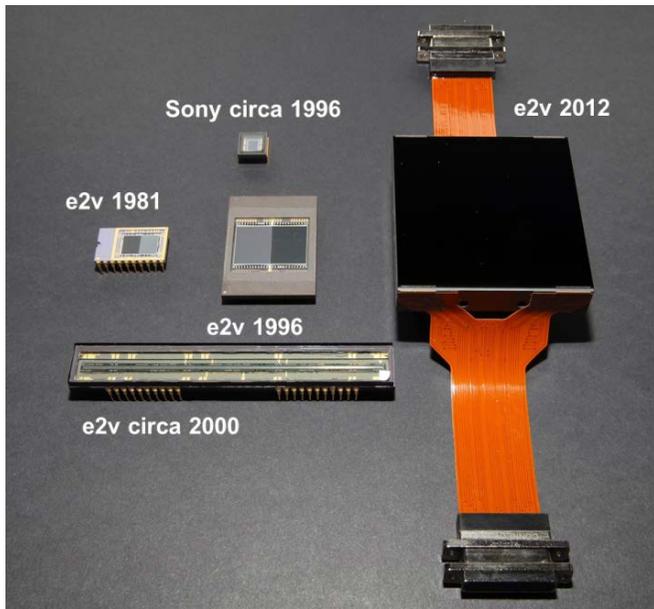
12.5 kHz clocking frequency (80 µs line-transfer time)

100% clock phase overlap

**Interphase coupling seen on the clock-lows and clock-highs**

# Conclusions and future plans

## New challenges in CCD sensors and focal planes



**GAIA Focal Plane** 106 CCDs ~ 938m pixels ~ 2800 cm<sup>2</sup>



**Kepler Focal Plane** 42 CCDs

# Conclusions and future plans

## Space-borne CCD camera design

- Programme of low- and high-voltage mixed-signal ASIC development
- Radiation-tolerant FPGA(s) for logic-level camera control

## Current packaging / qualification of the ASIC die

- Individual die packaged in standard CQFPs

## Future packaging / qualification options?

- Multi-die hybrid packaging technologies (multi-chip modules)
- Greater compactness
- Anticipated savings in overall packaging and qualification costs
- Possibly overly-custom and application-specific?
- Concern of impractically high power density?

## Increasing sophistication of space-borne CCD camera systems

- Large focal plane arrays of tiled CCDs with multiple video output ports
- Benefits of highly-integrated ASIC functionality and high-density packaging become increasingly attractive and necessary

# Thank you for your attention